NPN Silicon Planar Power Transistor 100VcBo, 15A lc, TO-3





RoHS Compliant

Applications

General Purpose Switching and Amplifier applications

Absolute Maximum Ratings (TA = 25 °C)

Description	Symbol	Value	Units	
Collector Base Voltage	Vсво	100		
Collector Emitter Voltage	VCEO 60			
Collector Emitter Voltage(RBE=100Ω)	VCER	70]	
Emitter Base Voltage	VEBO	7		
Collector Current Continuous	Ic	15	_	
Base Current	lв	7	A	
Power Dissipation @ Tc=25°C Derate Above 25°C	Ртот	115 0.657	W W/°C	
Operating and Storage Junction Temperature Range	ТJ, Tsтg	- 65 to +200	°C	

Thermal Characteristics

Characteristics	Symbol	Value	Unit
Junction-to-Case	R _{th(j-c)}	1.52	°C/W

Electrical Characteristics (TC=25°C unless specified otherwise)

Description	Symbol	Test Condition	Min.	Max.	Units
Collector Emitter Sustaining Voltage	VCEO(sus)*	Ic=200mA, Iв=0	60	-	V
Collector Emitter Sustaining Voltage	VCER(sus)*	Ic=200mA, RвE=100Ω	70	-	V
Collector Cut off Current	ICEX	VcE=100V, VBE=(off)=1.5V Tc=150°C VcE=100V, VBE=(off)=1.5V	-	1 5	mA
Collector Cut off Current	ICEO	Vce=30V, IB=0	-	0.7	
Emitter Cut off Current	ІЕВО	VBE=7V, IC=0	-	5	
Collector Emitter Saturation Voltage	VCE(Sat)*	Ic=4A, IB=400mA Ic=10A, IB=3.3A	-	1.1 3	V
Base Emitter on Voltage	VBE(on)*	Ic=4A, VcE=4V	-	1.5	
DC Current Gain	hFE*	Ic=4A, VcE=4V Ic=10A, VcE=4V	20 5	80	-

^{*}Pulse Test: Pulse Width ≤300µs, Duty Cycle ≤2%



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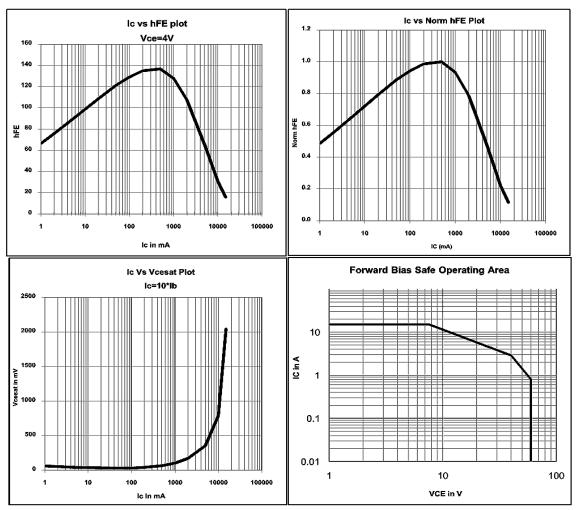
Second Breakdown

Description	Symbol	Test Condition	Min.	Max.	Units
Second Breakdown Collector Current with Base Forward Biased	ls/b	VcE=40V, t=1s, Nonrepetitive	2.87	-	А

Dynamic Characteristics

Description	Symbol	Test Condition	Min.	Max.	Units
Current Gain - Bandwidth Product	fτ	Ic=0.5A, VcE=10V, f=1MHz	2.5	-	MHz
Small Signal Current Gain	hFE	Ic=1A, VcE=4V, f=1kHz	15	120	-
Small Signal Current Gain Cutoff Frequency	fHFE	Ic=1A, VcE=4V, f=1kHz	10	-	kHz

Typical Characteristics Curves

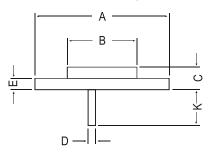


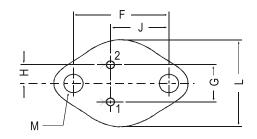
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Diagram

TO-3 Metal Can Package





Dim.	Min.	Max.
Α		39.37
В	_	22.22
С	6.35	8.5
D	0.96	1.09
E		1.77
F	29.9	30.4
G	10.69	11.18
Н	5.2	5.72
J	16.64	17.15
K	11.15	12.25
L	_	26.67
М	3.84	4.19



Pin Configuration

- 1. Base
- 2. Emitter
- 3. Collector

Part Number Table

Description	Part Number
NPN Silicon Planar Power Transistor, 15A, 100V, 115W	2N3055

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